

NTLUS4930N

MOSFET – Power, Single, N-Channel, μ Cool, UDFN6, 2.0x2.0x0.55 mm 30 V, 6.1 A

Features

- UDFN Package with Exposed Drain Pads for Excellent Thermal Conduction
- Low Profile UDFN 2.0 x 2.0 x 0.55 mm for Board Space Saving
- Low $R_{DS(on)}$ to Minimize Conduction Losses
- Low Capacitance to Minimize Driver Losses
- Optimized Gate Charge to Minimize Switching Losses
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

Applications

- Battery Switch
- Power Load Switch
- DC-DC Converters

MAXIMUM RATINGS ($T_J = 25^\circ\text{C}$ unless otherwise stated)

Parameter			Symbol	Value	Unit
Drain-to-Source Voltage			V_{DSS}	30	V
Gate-to-Source Voltage			V_{GS}	± 20	V
Continuous Drain Current (Note 1)	Steady State	$T_A = 25^{\circ}\text{C}$	I_D	6.1	A
		$T_A = 85^{\circ}\text{C}$		4.4	
	Continuous Drain Current (Note 1)	$t \leq 5\text{ s}$		$T_A = 25^{\circ}\text{C}$	
Power Dissipation (Note 1)	Steady State	$T_A = 25^{\circ}\text{C}$	P_D	1.65	W
	$t \leq 5\text{ s}$	$T_A = 25^{\circ}\text{C}$		3.8	
Continuous Drain Current (Note 2)	Steady State	$T_A = 25^{\circ}\text{C}$	I_D	3.8	A
		$T_A = 85^{\circ}\text{C}$		2.8	
Power Dissipation (Note 2)		$T_A = 25^{\circ}\text{C}$	P_D	0.65	W
Pulsed Drain Current		$t_p = 10\text{ }\mu\text{s}$	I_{DM}	19	A
MOSFET Operating Junction and Storage Temperature			T_J, T_{STG}	-55 to 150	$^{\circ}\text{C}$
Source Current (Body Diode) (Note 1)			I_S	1.65	A
Lead Temperature for Soldering Purposes (1/8" from case for 10 s)			T_L	260	$^{\circ}\text{C}$

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. Surface Mounted on FR4 Board using 1 in sq pad size (Cu area = 1.127 in sq [2 oz] including traces).
2. Surface-mounted on FR4 board using the minimum recommended pad size of 30 mm², 2 oz. Cu.

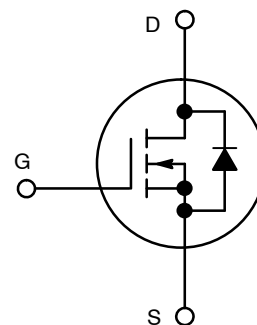


ON Semiconductor®

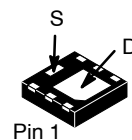
<http://onsemi.com>

MOSFET

$V_{(BR)DSS}$	$R_{DS(on)}$ MAX	I_D MAX
30 V	36 m Ω @ 4.5 V	6.1 A
	28.5 m Ω @ 10 V	5.5 A



N-CHANNEL MOSFET



MARKING DIAGRAM

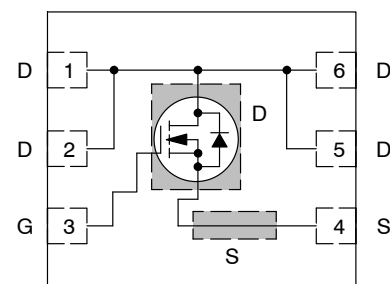
UDFN6
(μ COOL™)
CASE 517BG



AD = Specific Device Code
M = Date Code
▪ = Pb-Free Package

(*Note: Microdot may be in either location)

PIN CONNECTIONS



(Top View)

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 3 of this data sheet.

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THERMAL RESISTANCE RATINGS

Parameter	Symbol	Max	Unit
Junction-to-Ambient – Steady State (Note 3)	$R_{\theta JA}$	75.7	°C/W
Junction-to-Ambient – $t \leq 5$ s (Note 3)	$R_{\theta JA}$	32.9	
Junction-to-Ambient – Steady State min Pad (Note 4)	$R_{\theta JA}$	191.4	

3. Surface-mounted on FR4 board using 1 in sq pad size (Cu area = 1.127 in sq [2 oz] including traces).

4. Surface-mounted on FR4 board using the minimum recommended pad size of 30 mm², 2 oz. Cu.

ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test Condition	Min	Typ	Max	Units
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OFF CHARACTERISTICS

Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0$ V, $I_D = 250$ μ A	30			V
Drain-to-Source Breakdown Voltage Temperature Coefficient	$V_{(BR)DSS}/T_J$	$I_D = 250$ μ A, ref to 25°C		+16		mV/°C
Zero Gate Voltage Drain Current	I_{DSS}	$V_{GS} = 0$ V, $V_{DS} = 24$ V			1.0	μ A
Gate-to-Source Leakage Current	I_{GSS}	$V_{DS} = 0$ V, $V_{GS} = \pm 20$ V			10	μ A

ON CHARACTERISTICS (Note 5)

Gate Threshold Voltage	$V_{GS(TH)}$	$V_{GS} = V_{DS}$, $I_D = 250$ μ A	1.2	1.8	2.2	V
Negative Threshold Temp. Coefficient	$V_{GS(TH)}/T_J$			4.4		mV/°C
Drain-to-Source On Resistance	$R_{DS(on)}$	$V_{GS} = 10$ V, $I_D = 6.1$ A		19	28.5	m Ω
		$V_{GS} = 4.5$ V, $I_D = 5.5$ A		27	36	
Forward Transconductance	g_{FS}	$V_{DS} = 1.5$ V, $I_D = 6.0$ A		16		S

CHARGES, CAPACITANCES & GATE RESISTANCE

Input Capacitance	C_{ISS}	$V_{GS} = 0$ V, $f = 1$ MHz, $V_{DS} = 15$ V		476		pF
Output Capacitance	C_{OSS}			197		
Reverse Transfer Capacitance	C_{RSS}			100		
Total Gate Charge	$Q_{G(TOT)}$	$V_{GS} = 4.5$ V, $V_{DS} = 15$ V; $I_D = 5.5$ A		4.8		nC
Threshold Gate Charge	$Q_{G(TH)}$			0.4		
Gate-to-Source Charge	Q_{GS}			1.54		
Gate-to-Drain Charge	Q_{GD}			2.15		
	$Q_{G(TOT)}$	$V_{GS} = 10$ V, $V_{DS} = 15$ V; $I_D = 5.5$ A		8.7		nC

SWITCHING CHARACTERISTICS, $V_{GS} = 4.5$ V (Note 6)

Turn-On Delay Time	$t_{d(ON)}$	$V_{GS} = 4.5$ V, $V_{DD} = 15$ V, $I_D = 5.5$ A, $R_G = 3$ Ω		8.7		ns
Rise Time	t_r			14.4		
Turn-Off Delay Time	$t_{d(OFF)}$			9.1		
Fall Time	t_f			3.3		

SWITCHING CHARACTERISTICS, $V_{GS} = 10$ V (Note 6)

Turn-On Delay Time	$t_{d(ON)}$	$V_{GS} = 10$ V, $V_{DD} = 15$ V, $I_D = 6.1$ A, $R_G = 3$ Ω		4.1		ns
Rise Time	t_r			12.2		
Turn-Off Delay Time	$t_{d(OFF)}$			11.6		
Fall Time	t_f			2.2		

DRAIN-SOURCE DIODE CHARACTERISTICS

Forward Diode Voltage	V_{SD}	$V_{GS} = 0$ V, $I_S = 1.65$ A	$T_J = 25^\circ\text{C}$		0.80	1.0	V
			$T_J = 125^\circ\text{C}$		0.67		

5. Pulse Test: pulse width ≤ 300 μ s, duty cycle $\leq 2\%$.

6. Switching characteristics are independent of operating junction temperatures.

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ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise specified)

Parameter	Symbol	Test Condition	Min	Typ	Max	Units
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DRAIN-SOURCE DIODE CHARACTERISTICS

Reverse Recovery Time	t _{RR}	V _{GS} = 0 V, dI _S /dt = 100 A/μs, I _S = 3.3 A		14.6		ns
Charge Time	t _a			6.8		
Discharge Time	t _b			7.8		
Reverse Recovery Charge	Q _{RR}			5.4		nC

5. Pulse Test: pulse width ≤ 300 μs, duty cycle ≤ 2%.

6. Switching characteristics are independent of operating junction temperatures.

DEVICE ORDERING INFORMATION

Device	Package	Shipping [†]
NTLUS4930NTAG	UDFN6 (Pb-Free)	3000 / Tape & Reel
NTLUS4930NTBG	UDFN6 (Pb-Free)	3000 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

TYPICAL CHARACTERISTICS

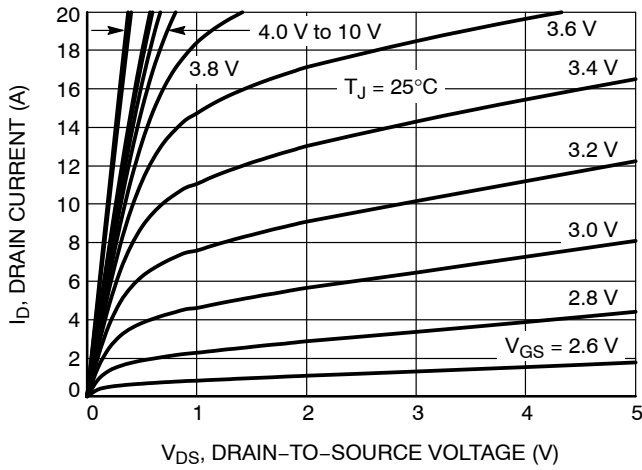


Figure 1. On-Region Characteristics

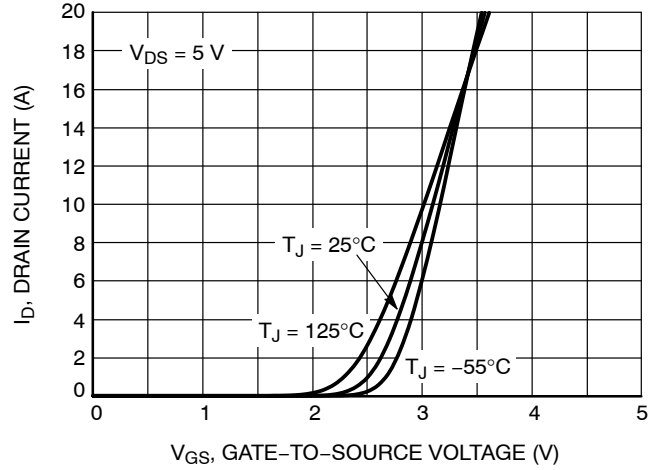


Figure 2. Transfer Characteristics

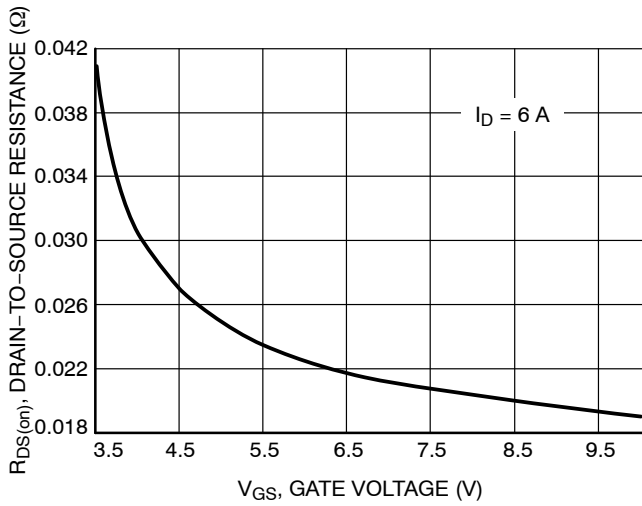


Figure 3. On-Resistance vs. Gate-to-Source Voltage

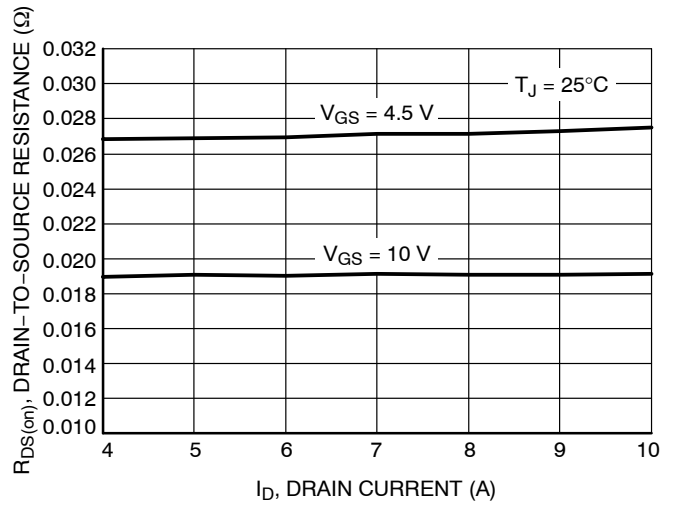


Figure 4. On-Resistance vs. Drain Current and Gate Voltage

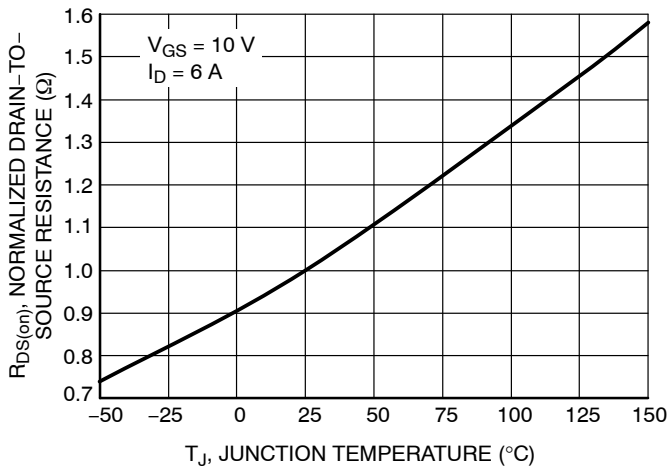


Figure 5. On-Resistance Variation with Temperature

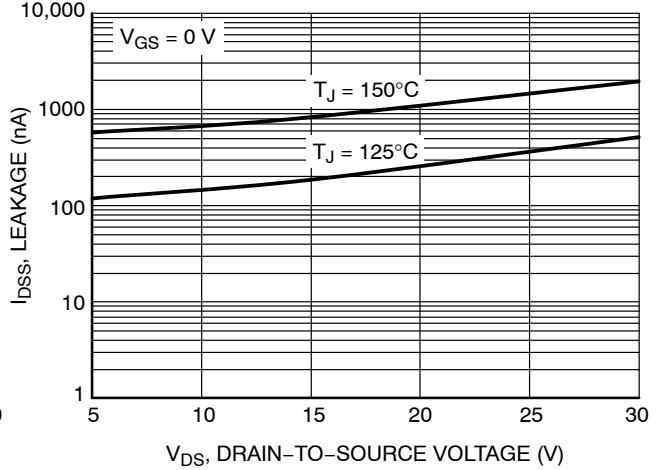


Figure 6. Drain-to-Source Leakage Current vs. Voltage

TYPICAL CHARACTERISTICS

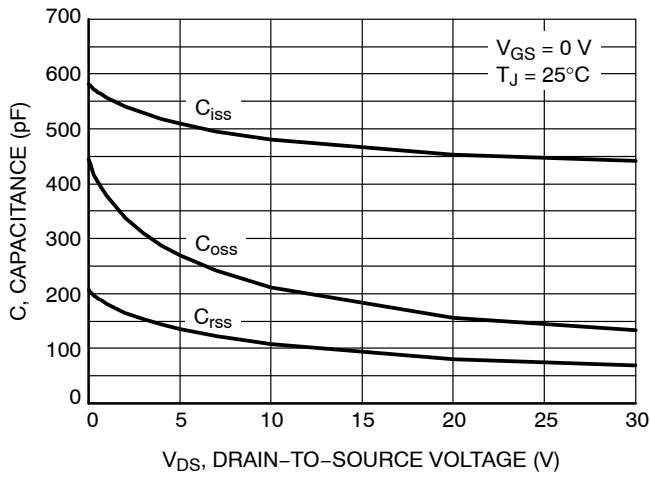


Figure 7. Capacitance Variation

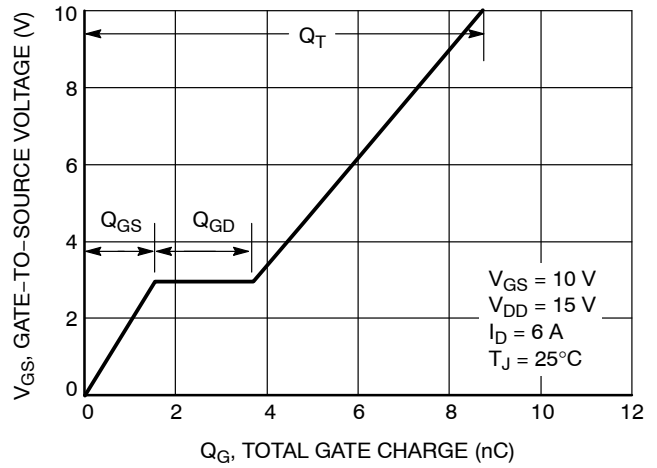


Figure 8. Gate-to-Source and Drain-to-Source Voltage vs. Total Charge

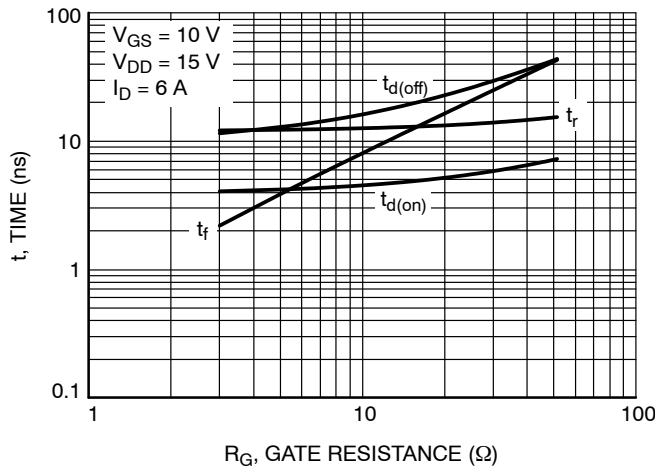


Figure 9. Resistive Switching Time Variation vs. Gate Resistance

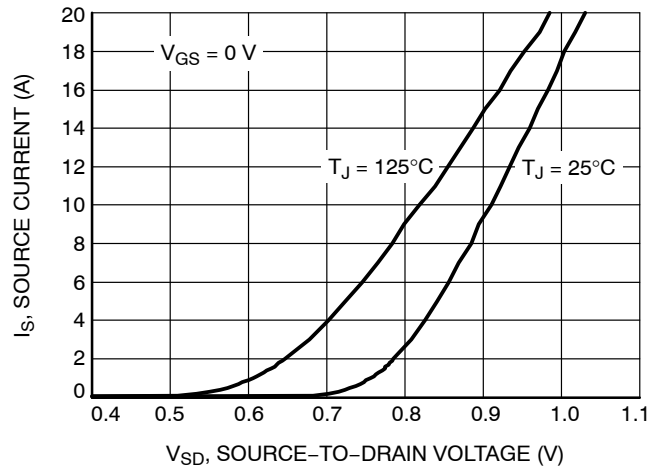


Figure 10. Diode Forward Voltage vs. Current

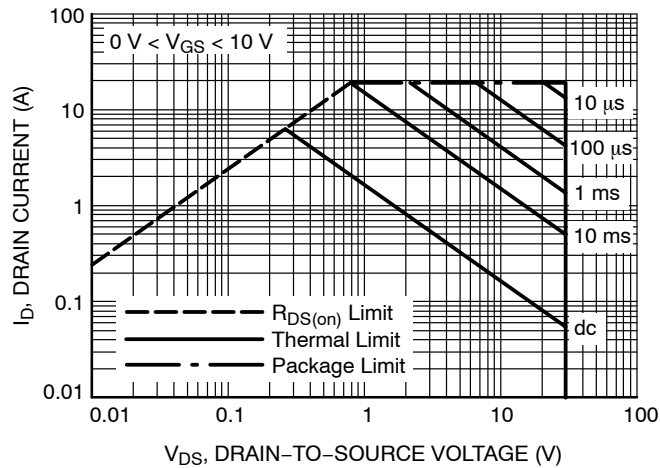
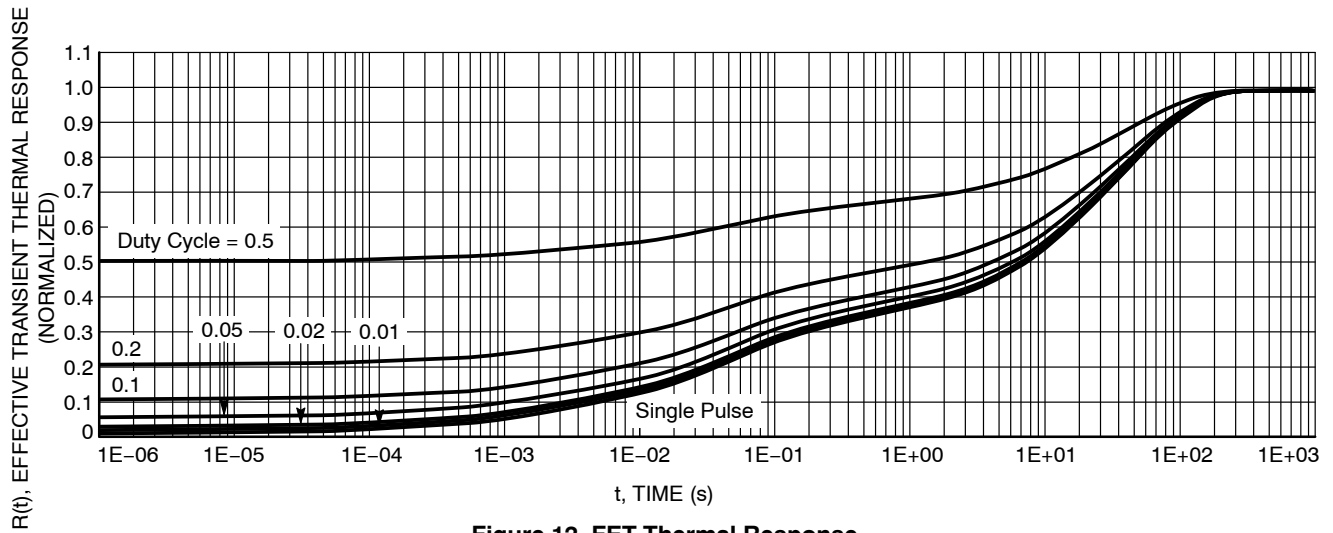


Figure 11. Maximum Rated Forward Biased Safe Operating Area

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TYPICAL CHARACTERISTICS



MECHANICAL CASE OUTLINE PACKAGE DIMENSIONS

ON Semiconductor®

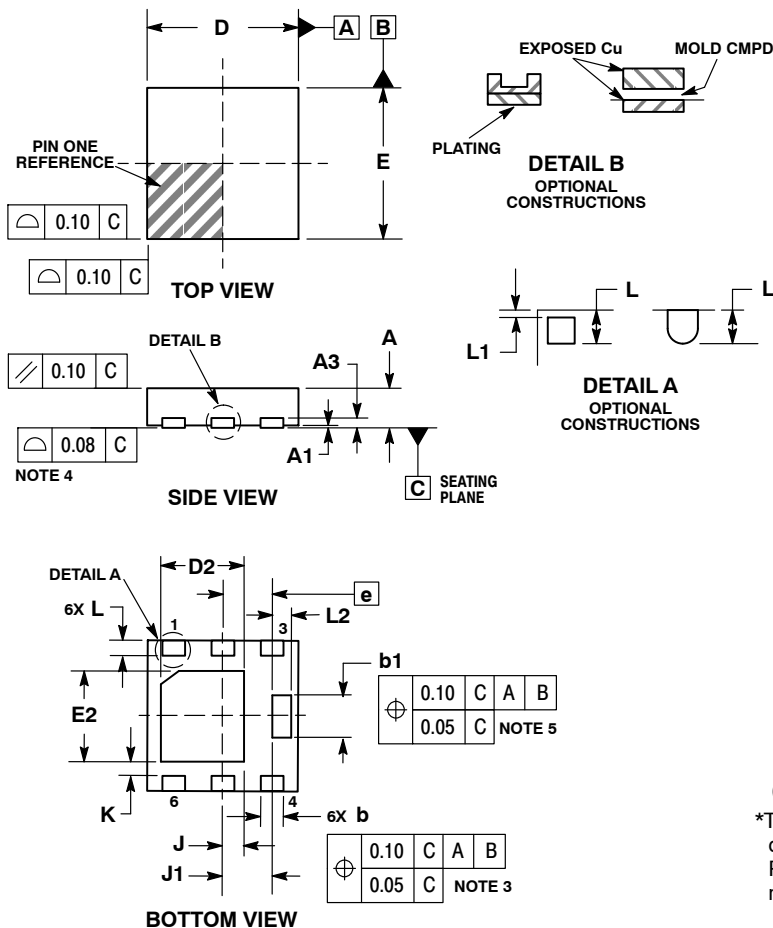
ON



SCALE 4:1

UDFN6 2x2, 0.65P
CASE 517BG-01
ISSUE A

DATE 04 FEB 2010



NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. DIMENSION b APPLIES TO PLATED TERMINAL AND IS MEASURED BETWEEN 0.15 AND 0.30 mm FROM TERMINAL.
4. COPLANARITY APPLIES TO THE EXPOSED PAD AS WELL AS THE TERMINALS.
1. CENTER TERMINAL LEAD IS OPTIONAL. CENTER TERMINAL IS CONNECTED TO TERMINAL LEAD # 4.
2. LEADS 1, 2, 5 AND 6 ARE TIED TO THE FLAG.

DIM	MILLIMETERS	
	MIN	MAX
A	0.45	0.55
A1	0.00	0.05
A3	0.13 REF	
b	0.25	0.35
b1	0.51	0.61
D	2.00 BSC	
D2	1.00	1.20
E	2.00 BSC	
E2	1.10	1.30
e	0.65 BSC	
K	0.15 REF	
J	0.27 BSC	
J1	0.65 BSC	
L	0.20	0.30
L1	---	0.10
L2	0.20	0.30

GENERIC MARKING DIAGRAM*



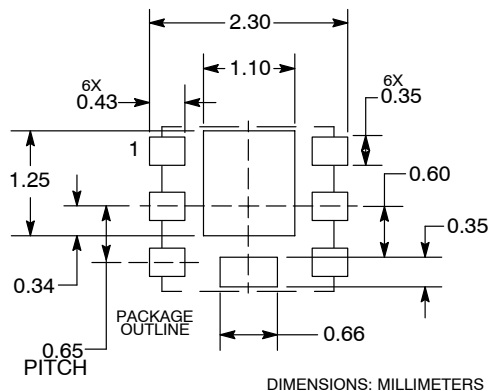
XX = Specific Device Code

M = Date Code

(Note: Microdot may be in either location)

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present.

RECOMMENDED MOUNTING FOOTPRINT



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DESCRIPTION:	UDFN6 2X2, 0.65P	PAGE 1 OF 1

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